VFPB010R080NA

Datasheet

General Description

The VMD VFPB010R080NA MOSFET is based on unique device design to achieve low RDS(ON), low gate charge, fast switching and excellent avalanche characteristics. The high V_{th} series is specially optimized for high systems with gate driving voltage greater than 10V.

Symbol

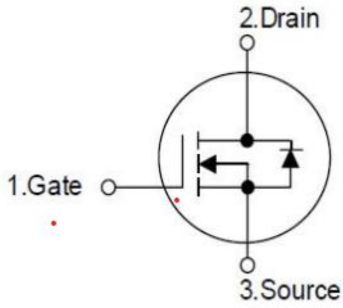
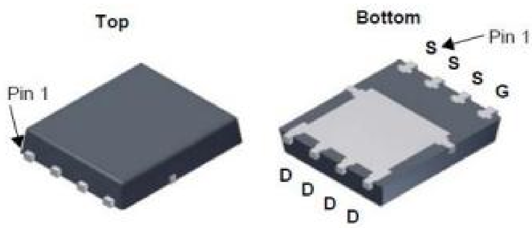


Figure 1 Symbol of VFPB010R080NA

Features

- Ultra Low $R_{DS(ON)\_max}$ = 8.0mΩ@V_{GS} = 10V.
- Extremely low switching loss
- Excellent stability and uniformity
- 100% UIS tested , 100% △VDS Tested
- RoHS and Halogen-Free Compliant

Package Type



DFN5*6

Figure 2 Package Type of VFPB010R080NA

Application

- Charger / Adapter
- Server/Telecom
- Synchronous Rectification
- High Frequency Switching

Ordering Information

Product Name	Package
VFPB010R080NA	PDFN5*6

Absolute Maximum Ratings

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current	T_C=25ºC(Note 5)	I_D	79	A
	T_C=100ºC(Note 5)		50	
Pulsed Drain Current (Note 3)		I_{DM}	316	A
Power Dissipation,T_C=25ºC(Note 2)		P_D	76	W
Avalanche Energy, Single Pulse (Note 3,Note6)		E_{AS}	108	mJ
Avalanche Current, Repetitive (Note 3,Note6)		I_{AS}	21	A
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to 150	ºC

Thermal Resistance

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$			1.65	ºC/W
Thermal Resistance, Junction-to-Ambient(Note 1,Note4)	$R_{\theta JA}$			55	ºC/W

Notes:

1. The value of $R_{\theta JC}$ is measured in a still air environment with TA =25°C and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
2. The power dissipation PD is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.
3. Single pulse width limited by junction temperature $T_{J(MAX)}$=150°C.
4. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
5. The maximum current rating is package limited.
6. The EAS data shows Max. rating. The test condition is V_{DS}=50V,V_{GS}=10V,L=0.5mH

Electrical Characteristics T_J= 25 ºC, unless otherwise specified

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Statistic Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250uA	100			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=80V, V_{GS}=0V			1	uA
Gate-Body Leakage Current — Forward	I_{GSSF}	V_{GS}=20V, V_{DS}=0V			100	nA
Gate-Body Leakage Current — Reverse	I_{GSSR}	V_{GS}=-20V, V_{DS}=0V			-100	nA
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=0.25mA	1.2	1.8	2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=20A		6.8	8.0	mΩ
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=4.5V, I_D=15A		8.5	10	mΩ
Gate Resistance	R_G	F=1MHz, Open Drain		1.89		Ω
Dynamic Characteristics						
Input Capacitance	C_{ISS}	V_{DS}=50, V_{GS}=0V, f=1MHz		2362		pF
Output Capacitance	C_{OSS}			743		pF
Reverse Transfer Capacitance	C_{RSS}			78		pF
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=50V, I_D=20A, R_G=3.0Ω,V_{GS}=10V		16		ns
Rise Time	t_r			6		
Turn-off Delay Time	$t_{d(off)}$			45		
Fall Time	t_f			22		
Gate Charge Characteristics						
Gate to Source Charge	Q_{gs}	V_{DD}=50V, I_D=20A, V_{GS}=10V		13		nC
Gate to Drain Charge	Q_{gd}			10		
Gate Charge Total	Q_g			42.2		
Reverse Diode Characteristics						
Continuous Source Current	I_S				79	A
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=20A		0.85	1.2	V
Reverse Recovery Time	t_{rr}	I_F=20A, dI_F/dt=100A/us		211		ns
Reverse Recovery Charge	Q_{rr}			84		nC

Typical Performance Characteristics

Figure 3: Maximum Power Dissipation vs Case Temperature

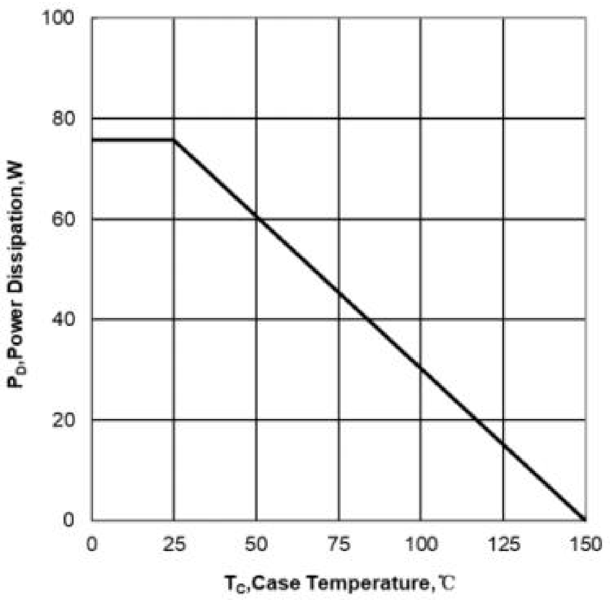


Figure 4: Gate Charge

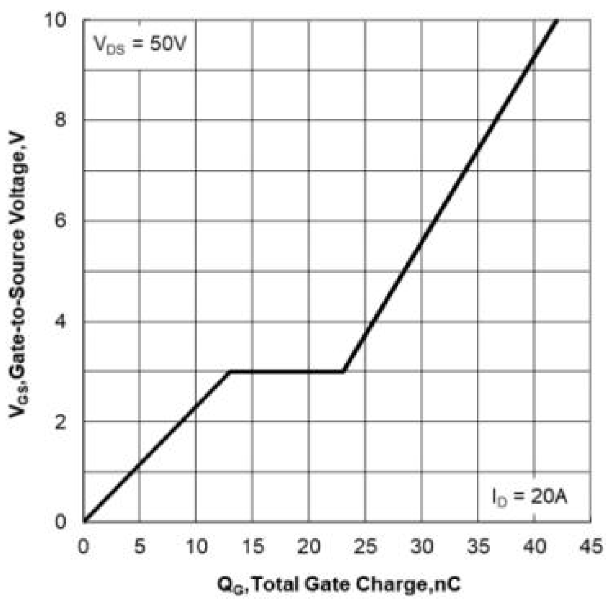


Figure 5: Maximum Continuous Drain Current vs Case Temperature

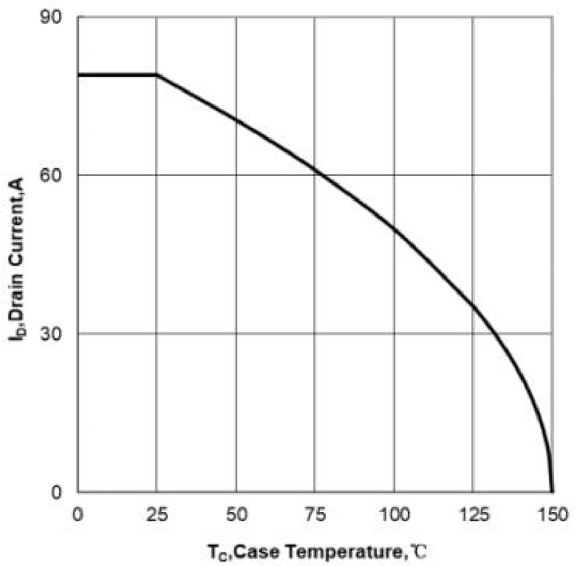


Figure 6: Output Characteristics

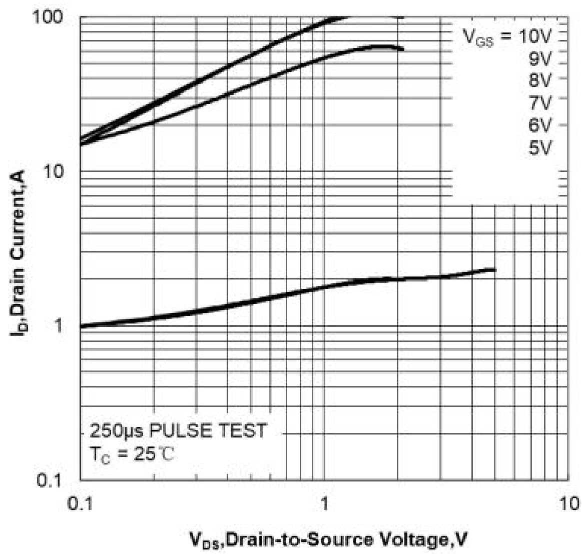


Figure 7: Drain-to-Source On Resistance vs Drain Current

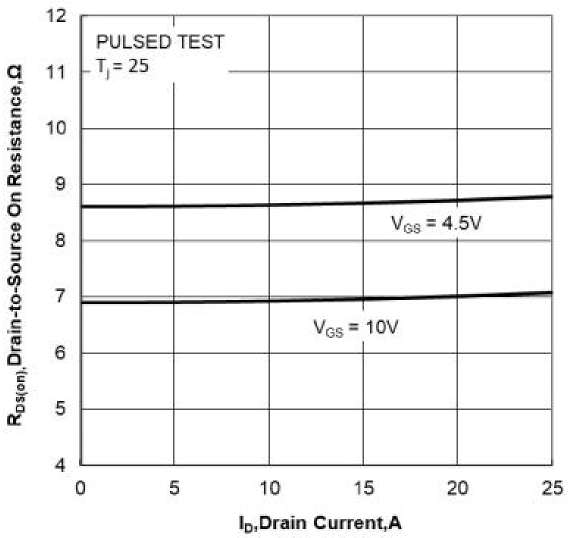


Figure 8: Transfer Characteristics

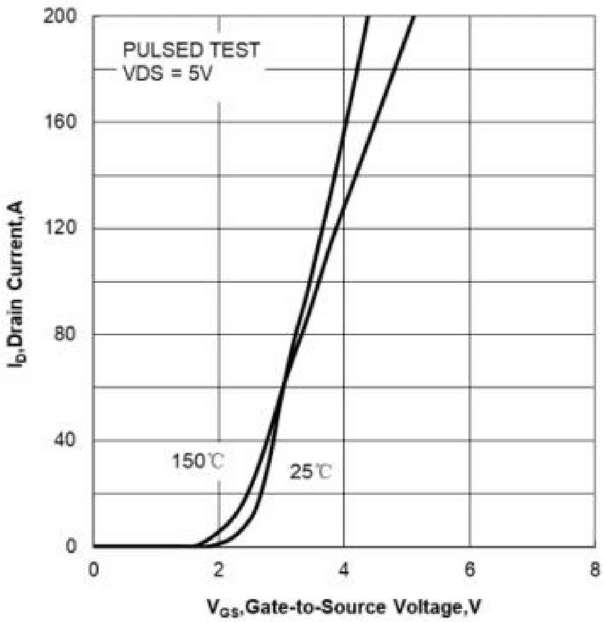


Figure 9: Body Diode Forward Voltage vs Source Current and Temperature

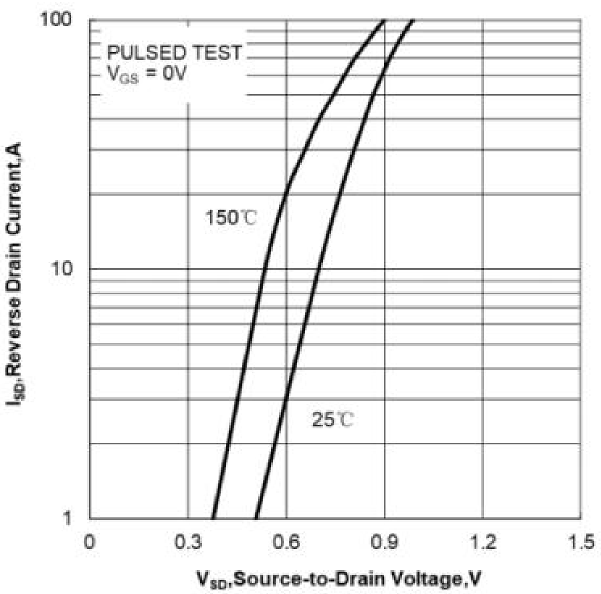


Figure 10: Capacitance Characteristics

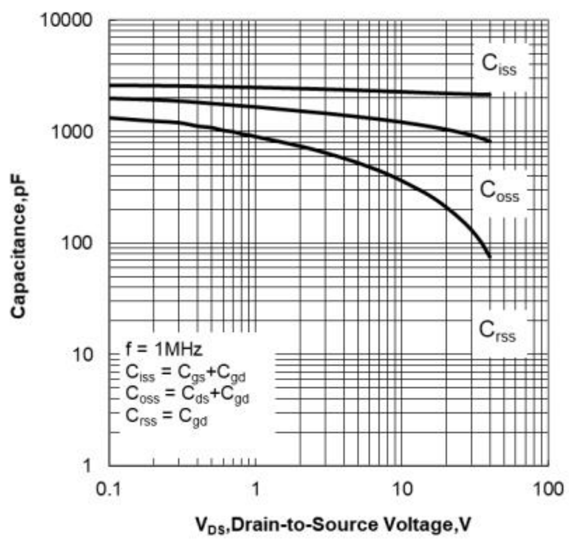


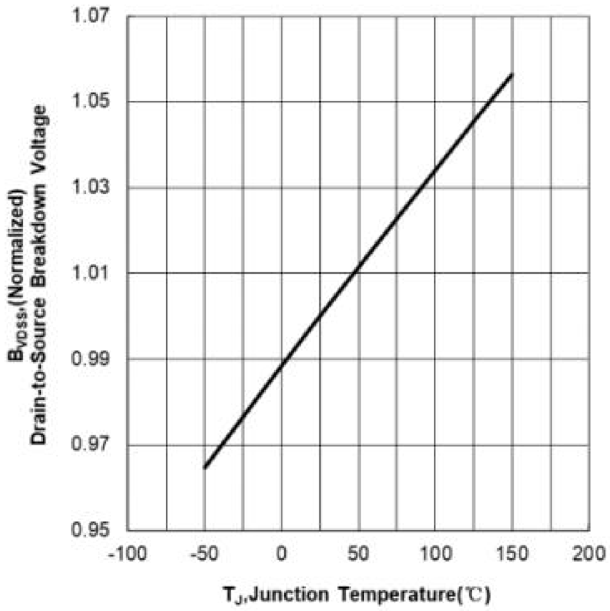
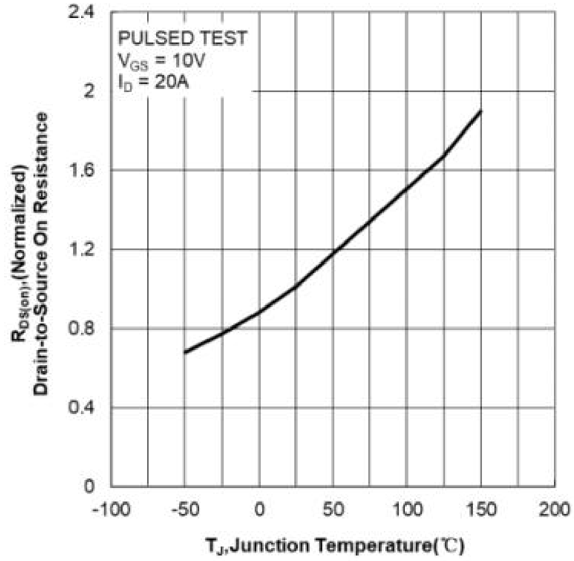
Figure 11: Normalized Breakdown Voltage vs Junction Temperature	Figure 12: Normalized On Resistance vs Junction Temperature
	

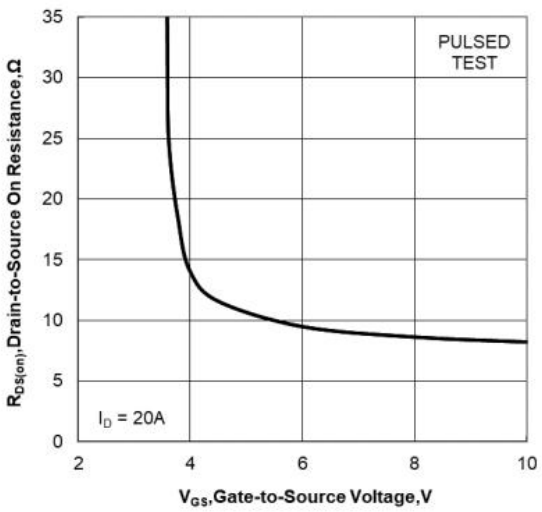
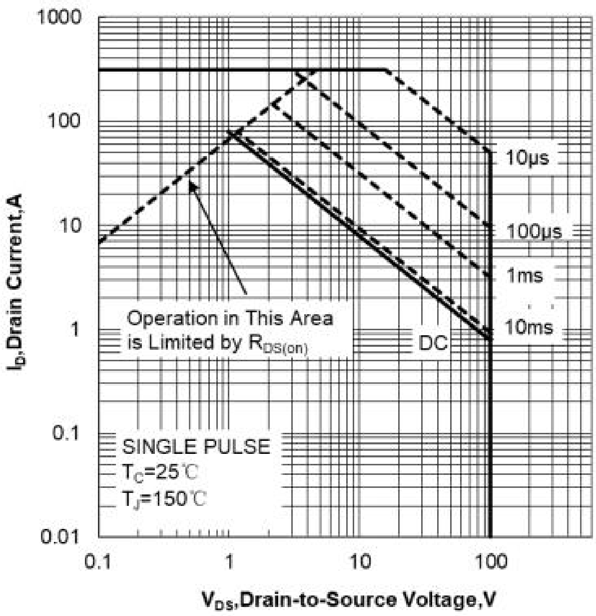
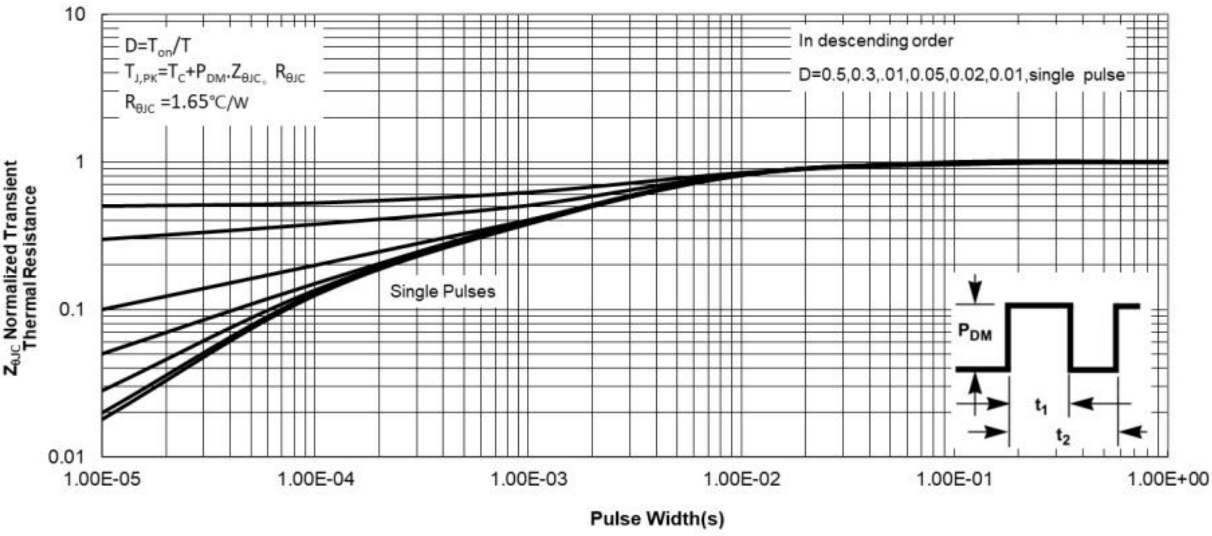
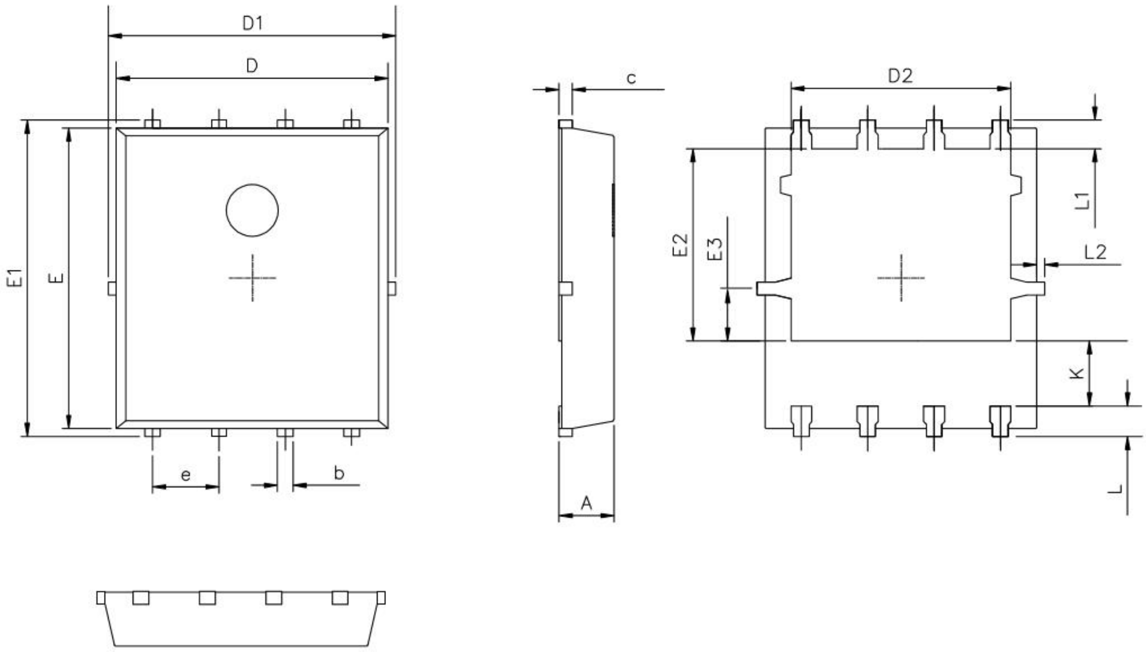
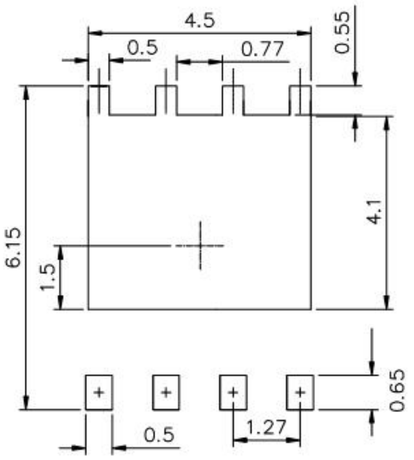
Figure 13: Drain-to-Source On Resistance vs Gate Voltage and Drain Current	Figure 14: Maximum Safe Operation Area
	

Figure 13: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Mechanical Dimensions （PDF5*6 Unit: mm）





Symbol	Dimensions(mm)		
	Min.	Typ.	Max.
A	0.9	1.0	1.10
b	0.25	0.35	0.50
c	0.10	0.20	0.30
D	4.80	5.00	5.30
D1	4.90	5.10	5.50
D2	3.92	4.02	4.20
E	5.65	5.75	5.85
E1	5.90	6.05	6.20
E2	3.325	3.525	3.775
E3	0.80	0.90	1.00
e		1.27	
L	0.40	0.55	0.70
L1		0.65	
L2	0.00		0.15
K	1.00	1.30	1.50

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